

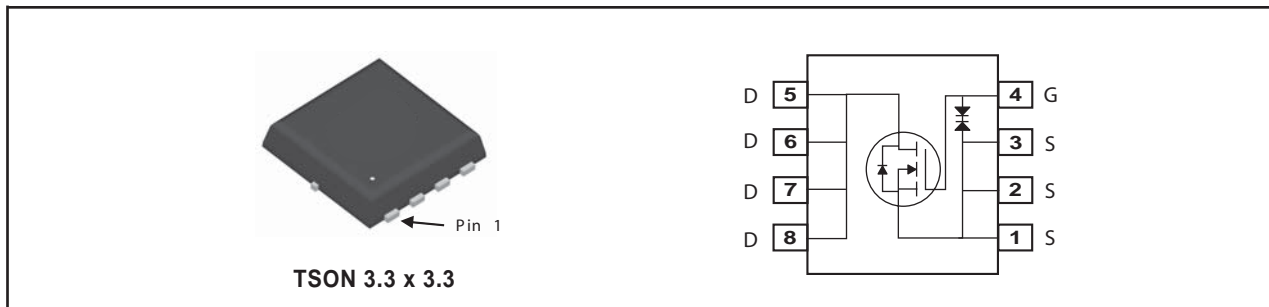


N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
30V	16A	19 @ V _{GS} =10V
		31 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^{a c}	T _C =25°C	16
		T _C =100°C	12.5
		T _A =25°C	7
		T _A =70°C	5.6
I _{DM}	-Pulsed ^c	60	A
E _{AS}	Single Pulse Avalanche Energy ^d	56	mJ
P _D	Maximum Power Dissipation ^a	T _A =25°C	1.67
		T _A =70°C	1.07
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient	75	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	4.8	°C/W

SP4412

Ver 1.1

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{bss}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.8	2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =3.5A		15	19	m ohm
		V _{GS} =4.5V , I _D =2.8A		23	31	m ohm
g _{FS}	Forward Transconductance	V _{DS} =5V , I _D =3.5A		14		S
DYNAMIC CHARACTERISTICS^b						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V f=1.0MHz		500		pF
C _{OSS}	Output Capacitance			120		pF
C _{RSS}	Reverse Transfer Capacitance			73		pF
SWITCHING CHARACTERISTICS^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =15V I _D =1A V _{GS} =10V R _{GEN} = 6 ohm		13		ns
t _r	Rise Time			12.5		ns
t _{D(OFF)}	Turn-Off Delay Time			19		ns
t _f	Fall Time			26		ns
Q _g	Total Gate Charge	V _{DS} =15V, I _D =3.5A, V _{GS} =10V		7		nC
		V _{DS} =15V, I _D =3.5A, V _{GS} =4.5V		3.8		nC
Q _{gs}	Gate-Source Charge	V _{DS} =15V, I _D =3.5A,		1.2		nC
Q _{gd}	Gate-Drain Charge	V _{GS} =10V		1.8		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A		0.75	1.2	V

Notes

- Surface Mounted on FR4 Board of 1 inch² , 1oz.
- Guaranteed by design, not subject to production testing.
- Drain current limited by maximum junction temperature.
- Starting T_J=25°C, L=0.5mH, V_{DD} = 20V. (See Figure13)

Apr,16,2014

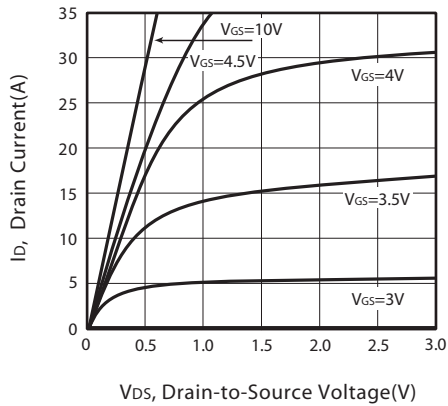


Figure 1. Output Characteristics

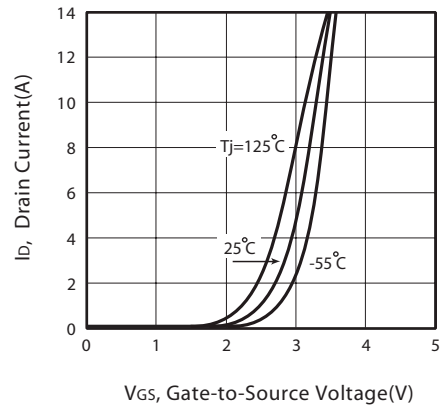


Figure 2. Transfer Characteristics

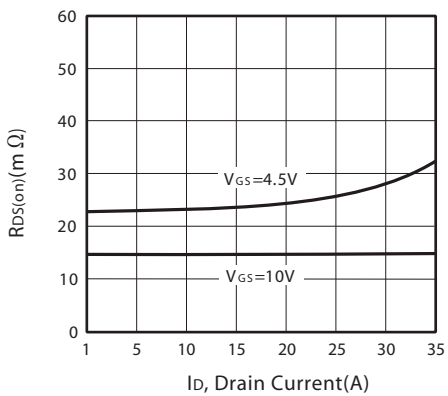


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

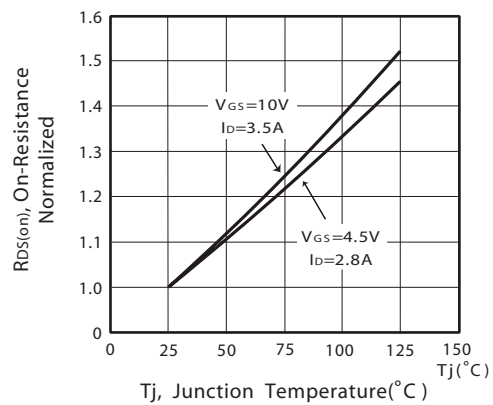


Figure 4. On-Resistance Variation with Drain Current and Temperature

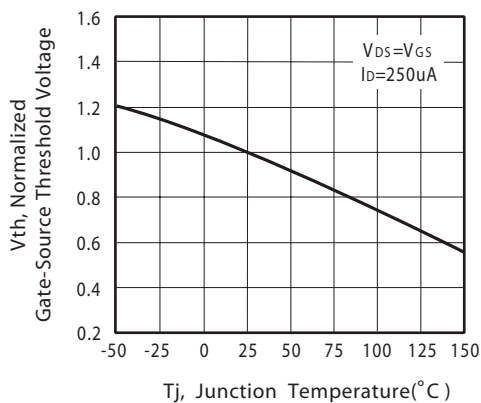


Figure 5. Gate Threshold Variation with Temperature

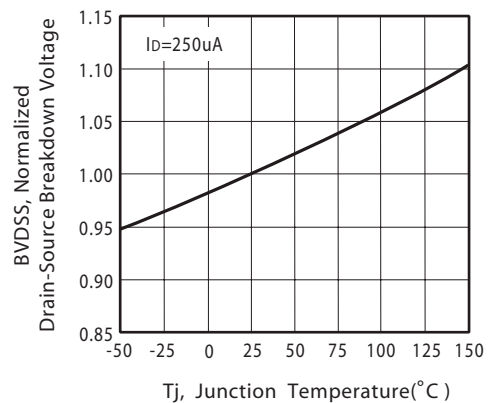


Figure 6. Breakdown Voltage Variation with Temperature

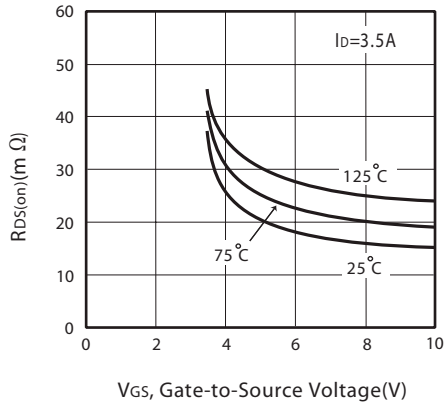


Figure 7. On-Resistance vs. Gate-Source Voltage

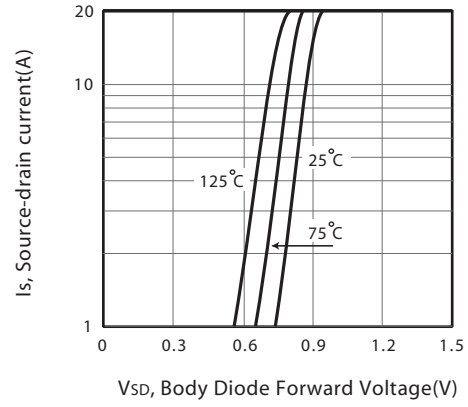


Figure 8. Body Diode Forward Voltage Variation with Source Current

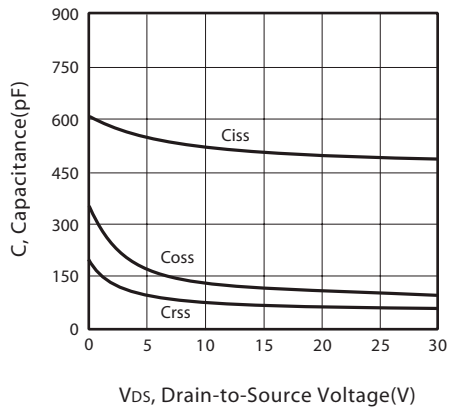


Figure 9. Capacitance

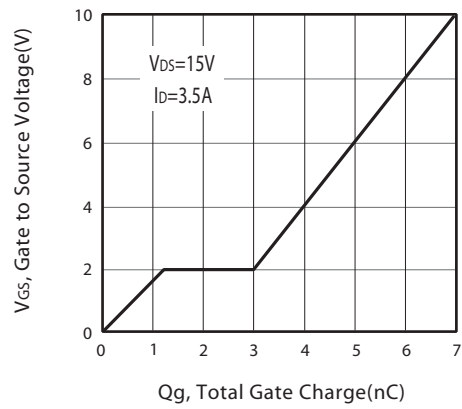


Figure 10. Gate Charge

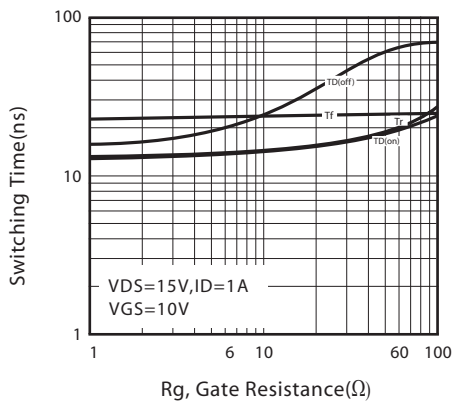


Figure 11. switching characteristics

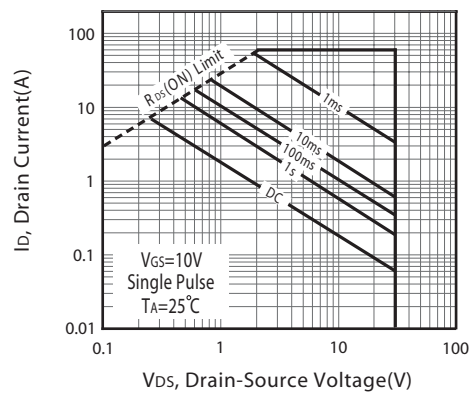
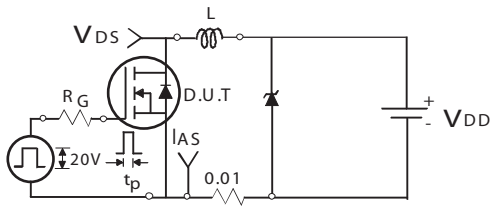
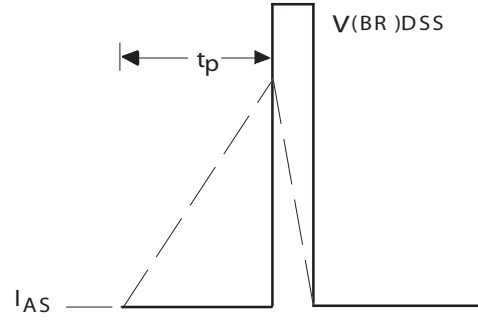


Figure 12. Maximum Safe Operating Area



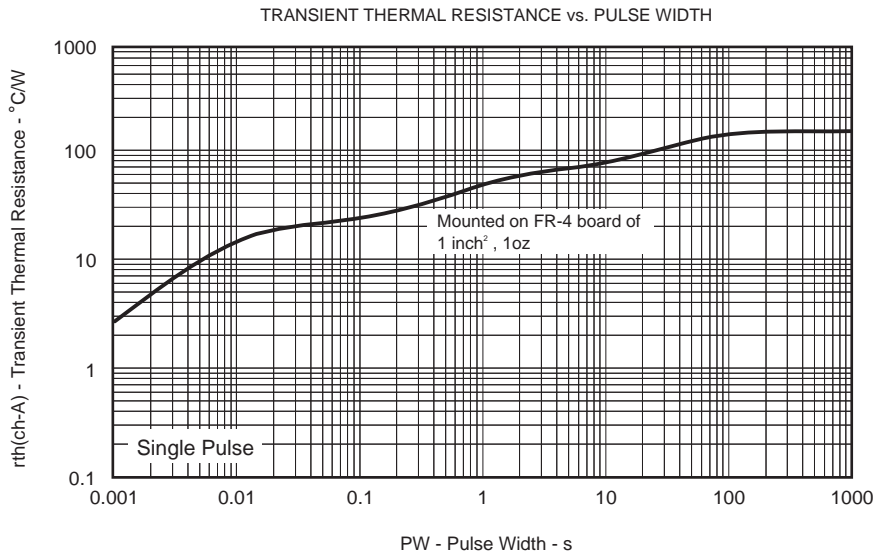
Unclamped Inductive Test Circuit

Figure 13a.



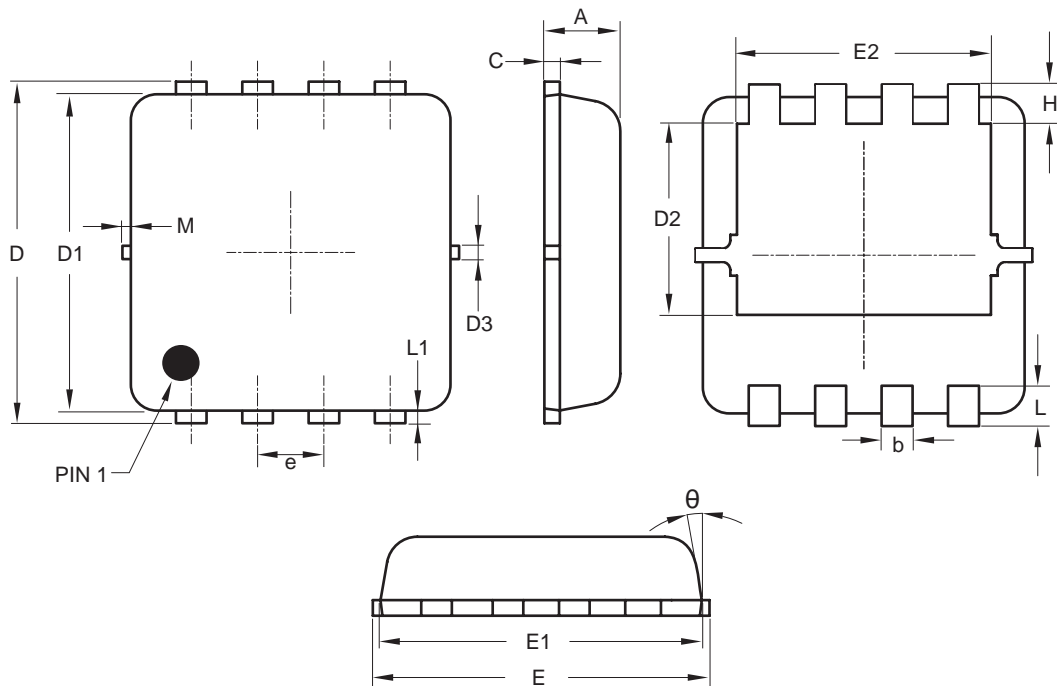
Unclamped Inductive Waveforms

Figure 13b.

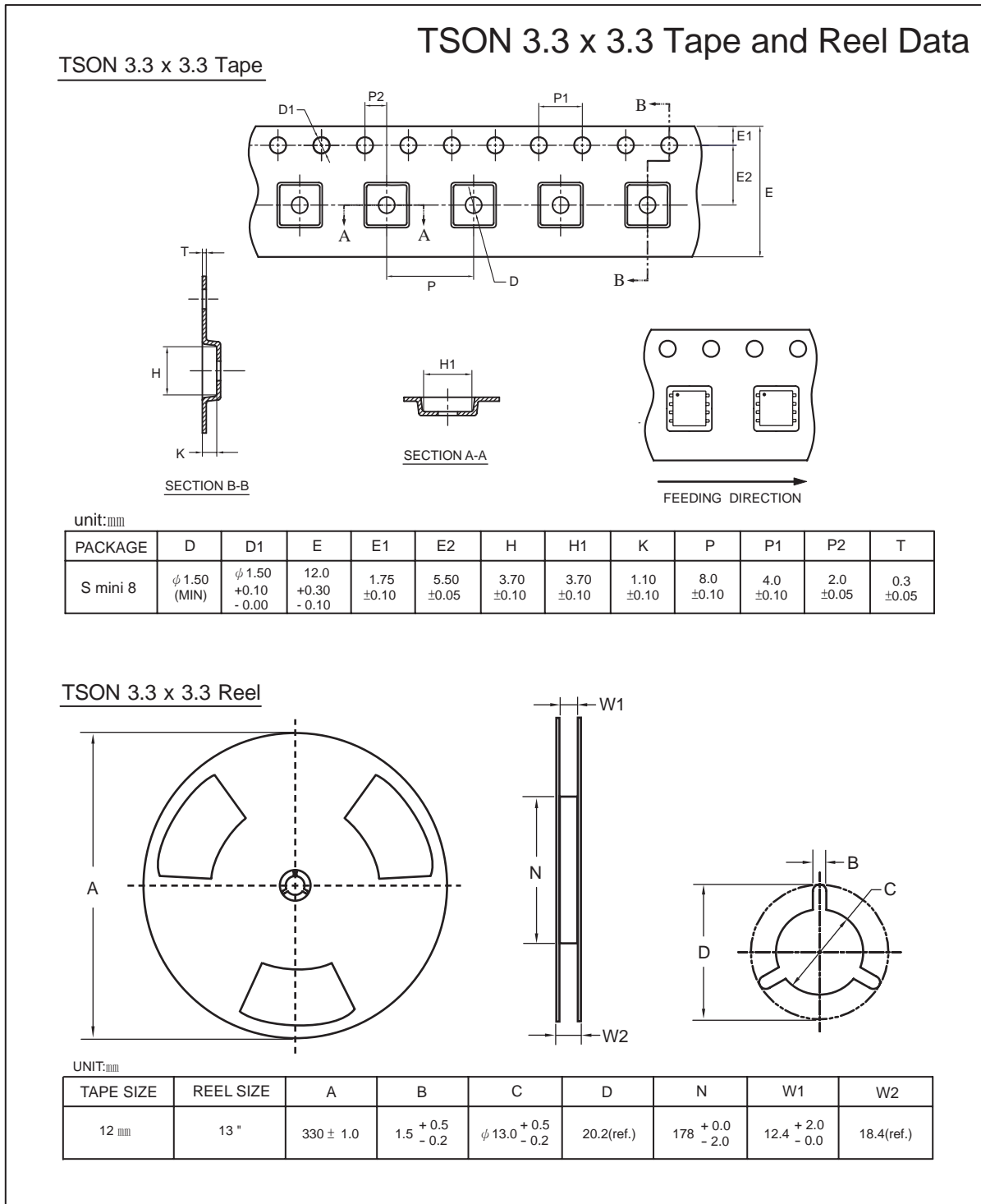


PACKAGE OUTLINE DIMENSIONS

TSON 3.3 x 3.3



SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
C	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	—	0.13	—
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65 BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	—	0.13	—
M	—	—	0.15
θ	—	10°	12°



TOP MARKING DEFINITION

